



U.S. Patent Application Serial No. 10/665,204  
Response filed September 18, 2006  
Reply to OA dated May 22, 2006

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1 - 16 (Canceled)

Claim 17 (Currently Amended): A semiconductor light-receiving device for a high-speed and large-capacity optical fiber communication system comprising:

a semi-insulating substrate;

a semiconductor layer of a first conduction type that is formed on the semi-insulating substrate;

a buffer layer of the first conduction type that is formed on the semiconductor layer;

a light absorption layer that is formed on the buffer layer and generates carriers in accordance with incident light;

a semiconductor layer of a second conduction type that is formed on the light absorption layer; and

a high-concentration semiconductor intermediate tunneling layer of the first conduction type that is interposed between the buffer layer and the light absorption layer and has a higher impurity concentration than the buffer layer, the semiconductor intermediate tunneling layer allowing

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electrons to pass therethrough to the buffer layer due to a tunnel effect, wherein said substrate and layers are arranged to form a semiconductor light-receiving device.

Claim 18 (Original): The semiconductor light-receiving device as claimed in claim 17, wherein the impurity concentration of the buffer layer is lower than  $1 \times 10^{17} \text{ cm}^{-3}$ .

Claim 19 (Previously Presented): The semiconductor light-receiving device as claimed in claim 17, wherein the high-concentration semiconductor intermediate tunneling layer has an impurity concentration of  $2 \times 10^{18} \text{ cm}^{-3}$ , and a film thickness of 100 nm or smaller.

Claim 20 (Currently Amended): The semiconductor light-receiving device as claimed in claim 17, further comprising a contact layer of the first conduction type that is interposed between the semi-insulating substrate and the buffer layer, the contact layer having a high impurity concentration, with a predetermined potential being supplied to the contact layer through an electrode connected to the contact layer.

Claim 21 (Original): The semiconductor light-receiving device as claimed in claim 17, wherein at least the light absorption layer and the semiconductor layer of the second conduction type form a mesa structure, with light entering the light absorption layer through a side surface of the light absorption layer that is exposed in a process of forming the mesa structure.

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Claim 22 (Canceled)

Claim 23 (Currently Amended): A semiconductor light-receiving device for a high-speed and large-capacity optical fiber communication system comprising:

a semiconductor substrate of a first conduction type;

a buffer layer of the first conduction type that is formed on the semiconductor substrate and has a lower impurity concentration than the semiconductor substrate;

a light absorption layer that is formed on the buffer layer and generates carriers in accordance with incident light;

a semiconductor layer of a second conduction type that is formed on the light absorption layer; and

a high-concentration semiconductor intermediate tunneling layer of the first conduction type that is interposed between the buffer layer and the light absorption layer and has a higher impurity concentration than the buffer layer, the semiconductor intermediate tunneling layer allowing electrons to pass therethrough to the buffer layer due to a tunnel effect, wherein said substrate and layers are arranged to form a semiconductor light-receiving device.